The Effect of Temperature on the Oxygen Sensing by Graphene

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Abstract- We have synthesized graphene using Hammers’ method. Then the Oxygen sensor is fabricated with qualified graphene nanosheets covered SiO$_2$/Si wafer and Ohmic contact in tow corners. Finally, we investigate the sensitivity of it when exposed to Oxygen at ambient condition in air and at different temperatures.

A resistive graphene-based gas sensor prepared in this way revealed $p$-type oxygen response at room temperature. So the absorption of Oxygen molecules on it increases the carrier density and cause to increase the electrical current across it. The variations of electrical current across the sensor, when exposed to Oxygen flow, get increased by increasing temperature.

Keywords: Oxygen sensor, graphene, sensitivity, ambient condition
1 Introduction

Graphene, a two-dimensional (2D) sp² carbon network, has attracted a wide range of interest due to its fascinating electronic, mechanical and thermal properties after its empirical discovery in 2004 [1]. The extremely high carrier mobility, mechanical flexibility, optical transparency and chemical stability of graphene provide great opportunities for the development of high-performance electronic and optoelectronic devices [2–11]. Among other applications, the exceptional surface-to-volume ratio and high electron mobility in room temperature entities graphene as a promising candidate for gas sensing applications. In this regard, the ultimate single-molecule sensitivity of graphene devices has been reported in recent years [12,13]. In addition to sensitivity and selectivity, sensor response is important in environmental conditions and under the interaction with surrounding atmospheric gases. Although Oxygen (O₂) is very important for life and industrial use, it can lead to combustion at high concentrations. Some researches show the ability of graphene to sense O₂ with very high sensitivity. In this work, we have used graphene for the fabrication of an O₂ sensor at ambient condition in air when exposed to O₂ gas and at different temperatures.

So, Hummers' method was utilized to oxidize natural graphite powder then the chemically oxidized graphite is cleaved to obtain graphene oxide nanosheets. Graphene nanosheets can be achieved by an additional reduction step. As-prepared sheets were characterized by the field emission scanning electron microscope (FESEM), FTIR spectrum and Raman scattering analysis. Then the O₂ sensor is fabricated with qualified graphene nanosheets covered SiO₂/Si wafer and Ohmic contact in tow corners. Finally, we investigate the sensitivity of it at ambient condition in air and under O₂ flow and at different temperatures.

2 Materials and method

In order to synthesize the graphite oxide, Hummers’ method was utilized to oxidize natural graphite powder. In this process, in a 250 mL flask 1 g of graphite and 1.5 g NaNO₃ were added to 25 mL of H₂SO₄. The flask was then placed in an ice bath for 15 min to cool it down to 0 °C. After that, 3 g of potassium permanganate (KMnO₄) was added slowly to the flask. The obtained suspension was then stirred continuously for 2 h. The temperature in this step was kept at 35°C. Subsequently, it was diluted by 200 mL of deionized (DI) water at the temperature less than 60°C. H₂O₂ solution was then added to flask over which the residual permanganate was reduced to soluble manganese ions. The obtained product was then isolated by filtration, washed copiously with DI water and dried at 60°C for 24 h to obtain brownish graphite oxide powder. In order to form a stable colloidal dispersion, a 10 mg portion of graphite oxide powder was dispersed in 10 mL of DI water by magnetic stirring for 1 h and sonication for 2 h [14, 15]. As a substrate for deposition of G sheets, (1 0 0) oriented silicon wafer was used. A 100 nm thickness of SiO₂ layer was then thermally grown on silicon substrate to electrically isolate the contacting electrodes from the substrate.

The Raman spectroscopy was used for characterization of the reduced sheets. Raman spectra were obtained at room temperature using a Nicolet Almega XR Dispersive Raman spectrometer equipped with second harmonic frequency of a Nd:YLF laser operating at 532 nm. Fourier transform infrared spectroscopy (FT-IR) was obtained using Bruker Tensor 27 Spectrometer to characterize the oxidized sheets. Morphological study of the samples was performed by a Hitachi 4160 FESEM at an electron accelerating voltage of 15 kV.

3 Results and Discussion

To characterize the surface topography of the prepared sheets by FESEM, graphene sheets were coated on the Si/SiO₂ substrate. Figures 1 show FESEM images of the prepared graphene sheets. Images present some partially overlapped sheets deposited on the substrate. As can be seen from Figures 2 and 3, the dimension of the majority of the sheets was found to be a few micrometers.

![Figure 1: FESEM images of the prepared G sheets on SiO2/Si substrate.](image-url)
1331, 1590 and 2898 cm\(^{-1}\). The G band shows the presence of sp\(^2\) carbon-type structures within the sample and the D band is associated with the presence of defects in the hexagonal graphitic layers [16–18].

To identify the bonds between C and O, FTIR analysis was carried out for graphene sheets on SiO\(_2\)/Si and Graphite Oxide powder prepared by Hammers’ method. The FTIR spectra show the presence of C-H, C=O, C-O-C, C-C and C=O at 900, 1020, 1123, 1583 and 1710 cm\(^{-1}\) respectively in Figure 3. The intensity of peaks is different for graphene layers and Graphite Oxide powder. Spatially, the appearance of a spread peak in the region of 3000 to 3600 cm\(^{-1}\) is seen in FTIR of Graphite Oxide powder that is related to the tensile vibration of the O-H bond [19, 20].

To test the applicability of the fabricated structure as O\(_2\) sensor, the electrical current variation during exposure of O\(_2\) at different temperatures were studied at ambient conditions in air. For this purpose, the current across the fabricated structure have been investigated versus the source-drain voltage before and after gas absorption at different temparatures. Then the differences between them are plotted at different temperatures versus source-drain voltage (Fig. 4).

![Figure 2: Raman spectroscopy of the prepared graphene sheets on SiO\(_2\)/Si substrate.](image)

The current of the sensor showed an increase when exposed to the O\(_2\) flow at ambient condition and room temperature. These current increases were due to the absorption of O\(_2\) molecules on graphene surface. They act as p-type dopants and enhanced the hole conduction and generate a significant increase in current. At higher temperature, the absorption rate of O\(_2\) on the surface of graphene increases and so the response of sensor to O\(_2\) flow becomes stronger.

![Figure 4: Variations of electrical current across the sensor, when exposed to Oxygen flow at different temperature.](image)

In conclusion, the current that is passing from the graphene sensor changes when expose to the O\(_2\) flow at ambient condition. By increasing temperature the sensitivity of graphene for O\(_2\) sensing gets increased.

**References**